

0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package

Rev. 02 — 13 January 2010

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT23 small Surface Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		Configuration	
	NXP	JEITA		
PMEG2005ET	SOT23	-	single diode	
PMEG3005ET	SOT23	-	single diode	
PMEG4005ET	SOT23	-	single diode	

1.2 Features

- Forward current: 0.5 A
- Very low forward voltage
- Small SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications



1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _F	forward current		-	-	0.5	Α
V_R	reverse voltage					
	PMEG2005ET		-	-	20	V
	PMEG3005ET		-	-	30	V
	PMEG4005ET		-	-	40	V
V _F	forward voltage	$I_F = 500 \text{ mA}$	<u>[1]</u>			
	PMEG2005ET		-	355	390	mV
	PMEG3005ET		-	380	430	mV
	PMEG4005ET		-	420	470	mV

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	anode		
2	not connected	<u> 3</u>	1 2
3	cathode	1 2	3 mlc357

3. Ordering information

Table 4. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PMEG2005ET	-	plastic surface mounted package; 3 leads	SOT23			
PMEG3005ET	-	plastic surface mounted package; 3 leads	SOT23			
PMEG4005ET	-	plastic surface mounted package; 3 leads	SOT23			

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4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PMEG2005ET	P3*
PMEG3005ET	P4*
PMEG4005ET	P5*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage				
	PMEG2005ET		-	20	V
	PMEG3005ET		-	30	V
	PMEG4005ET		-	40	V
I _F	forward current		-	0.5	Α
I_{FRM}	repetitive peak forward current	$t_p \leq \text{1 ms; } \delta \leq 0.5$	-	3.9	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms square wave	[1] -	10	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	280	mW
			[2] _	420	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from	in free air	[1][2]	-	440	K/W	
	junction to ambient		[1][3]	-	300	K/W

^[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating will be available on request.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

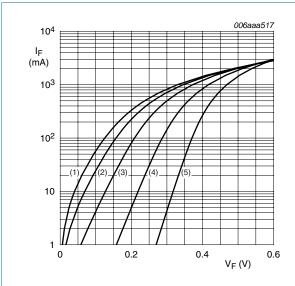
Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
	PMEG2005ET	$I_F = 0.1 \text{ mA}$	-	90	130	mV
		I _F = 1 mA	-	150	190	mV
		I _F = 10 mA	-	210	240	mV
		I _F = 100 mA	-	280	330	mV
		$I_F = 500 \text{ mA}$	-	355	390	mV
	PMEG3005ET	$I_F = 0.1 \text{ mA}$	-	90	130	mV
		I _F = 1 mA	-	150	200	mV
		I _F = 10 mA	-	215	250	mV
		I _F = 100 mA	-	285	340	mV
		$I_F = 500 \text{ mA}$	-	380	430	mV
	PMEG4005ET	$I_F = 0.1 \text{ mA}$	-	95	130	mV
		$I_F = 1 \text{ mA}$	-	155	210	mV
		I _F = 10 mA	-	220	270	mV
		I _F = 100 mA	-	295	350	mV
		$I_F = 500 \text{ mA}$	-	420	470	mV
R	reverse current					
יוּ	PMEG2005ET	V _R = 10 V	-	15	40	μΑ
		V _R = 20 V	-	40	200	μΑ
	PMEG3005ET	V _R = 10 V	-	12	30	μΑ
		V _R = 30 V	-	40	150	μΑ
	PMEG4005ET	V _R = 10 V	-	7	20	μΑ
		V _R = 40 V	-	30	100	μΑ
C_d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$				
	PMEG2005ET		-	66	80	pF
	PMEG3005ET		-	55	70	pF
	PMEG4005ET		-	43	50	pF

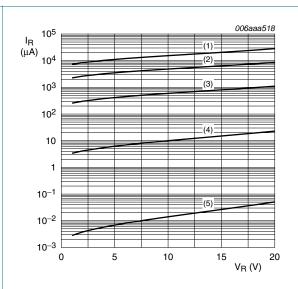
^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

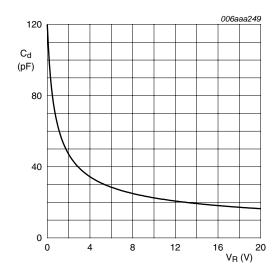




- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \,^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

PMEG2005ET: Reverse current as a function of Fig 2. reverse voltage; typical values

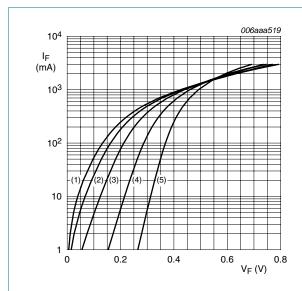
5 of 12



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

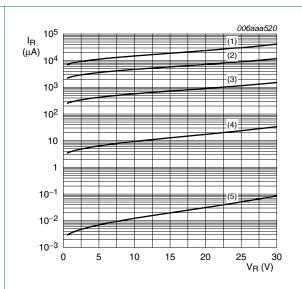
PMEG2005ET: Diode capacitance as a function of reverse voltage; typical values Fig 3.

0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package



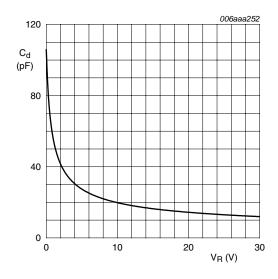
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
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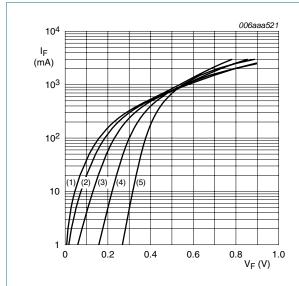
Fig 5. PMEG3005ET: Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \,^{\circ}C$; $f = 1 \, MHz$

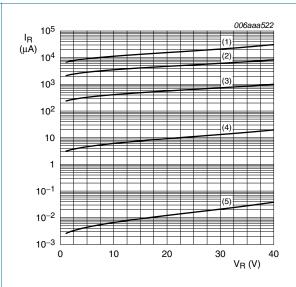
Fig 6. PMEG3005ET: Diode capacitance as a function of reverse voltage; typical values

0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package



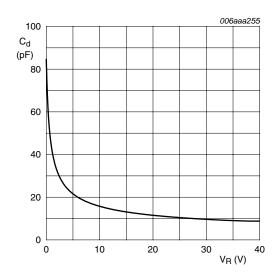
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$





- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \,^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

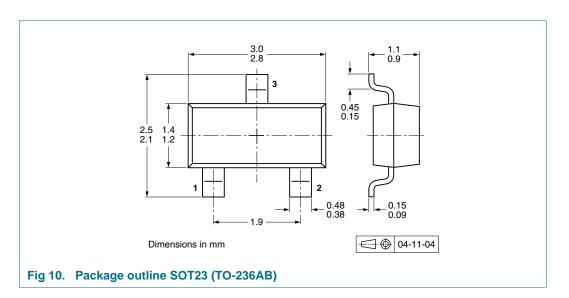
Fig 8. PMEG4005ET: Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

Fig 9. PMEG4005ET: Diode capacitance as a function of reverse voltage; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

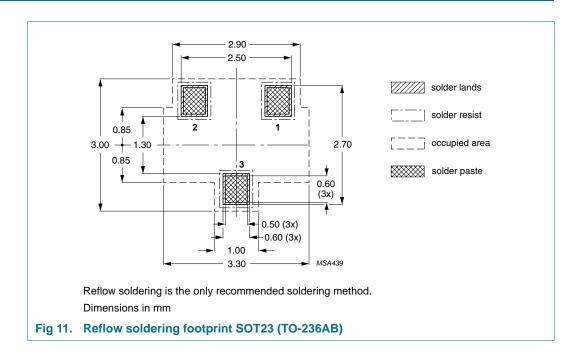
The -xxx numbers are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEG2005ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PMEG3005ET				
PMEG4005ET	_			

^[1] For further information and the availability of packing methods, see Section 13.

0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package

10. Soldering



0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PMEGXX05ET_SER_2	20100113	Product data sheet	-	PMEGXX05ET_SER_1	
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 11 "Reflow soldering footprint SOT23 (TO-236AB)": updated 				
	Figure 11 Re	enow soldering lootprint St	<u> Л23 (ТО-236АВ)</u> . up	uaieu	
PMEGXX05ET_SER_1	20050715	Product data sheet	-	-	

0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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0.5 A very low V_F MEGA Schottky barrier rectifiers in SOT23 package

14. Contents

1	Product profile	_ 1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	2
2	Pinning information	2
3	Ordering information	2
4	Marking	3
5	Limiting values	3
6	Thermal characteristics	3
7	Characteristics	4
8	Package outline	8
9	Packing information	8
10	Soldering	9
11	Revision history	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	11
13	Contact information	11
14	Contents	12

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